

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	47630	(thickness) near15 (thin near5 layer)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:35
2	BRS	L2	1348	(thickness) near15 (thin near5 semiconductor near3 layer)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:36
3	BRS	L3	148	((thickness) near15 (thin near5 semiconductor near3 layer)) near25 (oxid\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:36

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	20	((thickness) near15 (thin near5 semiconductor near3 layer)) near25 (oxidation)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:44
5	BRS	L5	0	((thickness) near15 (specification) near15 (semiconductor near3 layer)) near25 (oxidation)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:45
6	BRS	L6	1	((thickness) near15 (characteristic\$1) near15 (semiconductor near3 layer)) near25 (oxidation)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:46

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L8	9	((thickness) near5 (specification)) near25 (oxidation)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:46
8	BRS	L7	13	((thickness) near15 (specification)) near25 (oxidation)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:52
9	BRS	L9	350	((thickness) near15 (characteristic\$1)) near25 (oxidation)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:52

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	0	((sdjust\$3 near5 thickness) near15 (characteristic\$1)) near25 (oxidation)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:52
11	BRS	L11	3	((adjust\$3 near5 thickness) near15 (characteristic\$1)) near25 (oxidation)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 15:55
12	BRS	L12	20	((adjust\$3 near5 thickness) near15 (characteristic\$1)) near25 (oxid\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 16:04

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	14	((adjust\$3 near5 thickness) near15 (specif\$3)) near25 (oxid\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 16:08
14	BRS	L14	3029	((thickness) near15 (specif\$3)) near25 (oxid\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 16:08
15	BRS	L15	9	(measur\$3 or adjust\$3) near10 ((thickness) near15 (specif\$3)) near25 (oxidation)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 16:10

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	16	(measur\$3 or adjust\$3) near10 ((thickness) near15 (characteristic\$1)) near25 (oxidation)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 16:12
17	BRS	L17	5	(measur\$3 or adjust\$3) near10 ((thickness) near15 (characteristic\$1)) near25 (oxidized)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 16:13
18	BRS	L18	0	(measur\$3 or adjust\$3) near10 ((thickness) near15 (profile)) near25 (oxidized)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 16:13

	Type	L #	Hits	Search Text	DBs	Time Stamp
19	BRS	L19	1	(measur\$3 or adjust\$3) near10 ((thickness) near15 (specif\$3)) near25 (oxidized)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 9 16:14

	<b>U</b>	<b>1</b>	<b>Document ID</b>	<b>Title</b>	<b>Current OR</b>
1			US 20030232503 A1	Method for manufacturing semiconductor device	438/700
2			US 20020011176 A1	Electroless copper plating bath, electroless copper plating method and electronic part	106/1.23
3			US 6825128 B2	Method for manufacturing semiconductor device	438/750
4			US 6660071 B2	Electroless copper plating bath, electroless copper plating method and electronic part	106/1.23
5			US 6528433 B2	Method for monitoring nitrogen processes	438/786
6			JP 08050365 A	PRODUCTION OF ELECTROPHOTOGRAPHIC PHOTORECEPTOR	
7	X		JP 62269314 A	MANUFACTURE OF SEMICONDUCTOR DEVICE	
8	X		JP 58137755 A	MEASURING METHOD OF SOUNDNESS OF ZIRCONIUM ALLOY IN NUCLEAR REACTOR	

	<b>U</b>	<b>1</b>	<b>Document ID</b>	<b>Title</b>	<b>Current OR</b>
9	X		GB 2308733 A	Controlled oxide film formation on semiconductor device - includes calculating time required to grow certain thickness of oxide film based on inputted desired thickness and data from previous oxidation process, growing film, repeatedly measuring thickness, etc.	